CHINA BASE INTERNATIONAL

SOD-123

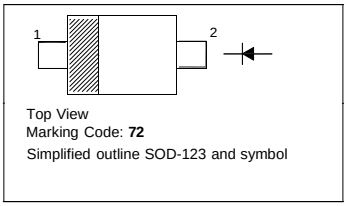
RB161M-20

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1A Schottky Barrier Diode

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Top View
Marking Code: **72**
Simplified outline SOD-123 and symbol

●Applications

General rectification

●Features

1)Small power mold type.
2)Low V_F
3)High reliability

●Construction

Silicon epitaxial planar

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	20	V
Average Forward Rectified Current	$I_{F(AV)}$	1	A
Non-Repetitive Peak Forward Surge Current (8.3 ms Single Half Sine-Wave)	I_{FSM}	9	A
Power Dissipation	P_{tot}	250	mW
Operating Temperature Range	T_j	- 55 to + 125	°C
Storage Temperature Range	T_{stg}	- 55 to + 125	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at I_R = 1 mA	$V_{(BR)R}$	20	-	V
Reverse Current at V_R = 20 V	I_R	-	1	mA
Forward Voltage at I_F = 1 A	V_F	-	0.45	V
Total Capacitance at V_R = 4 V, f = 1 MHz	C_{tot}	-	120	pF

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FIG. 1- FORWARD CURRENT DERATING CURVE

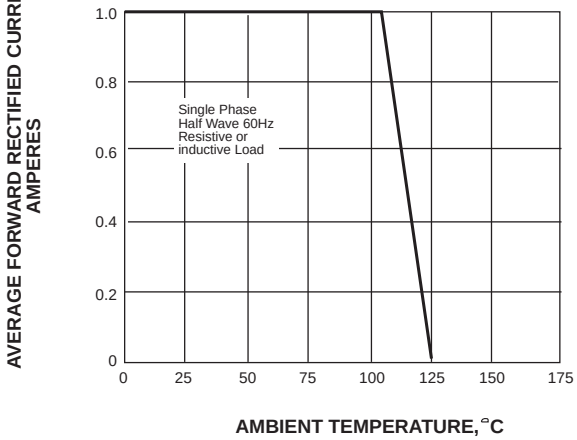


FIG. 2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

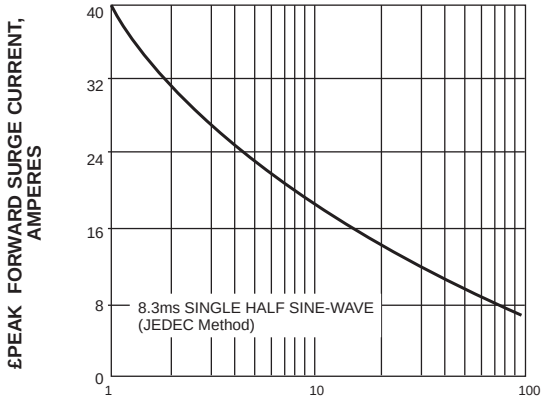


FIG. 3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

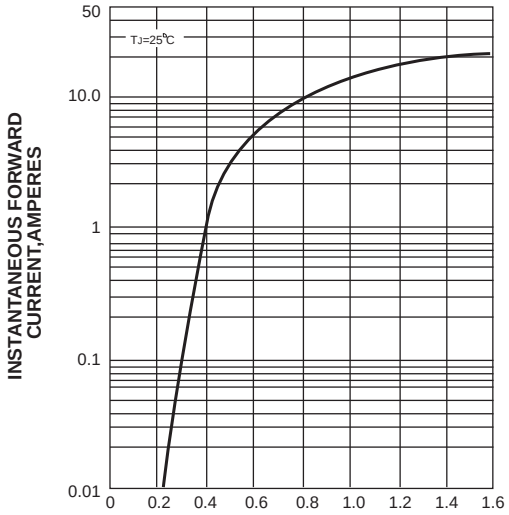


FIG. 4-TYPICAL REVERSE CHARACTERISTICS

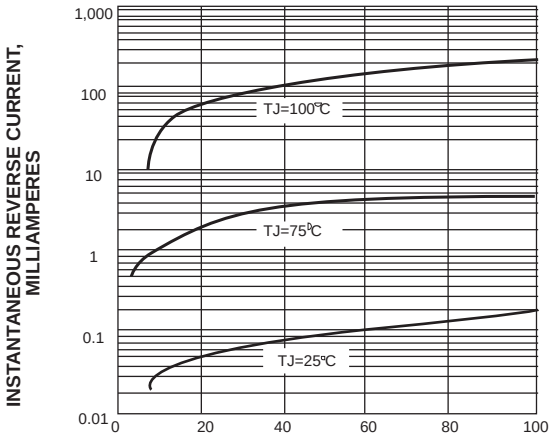


FIG. 5-TYPICAL JUNCTION CAPACITANCE

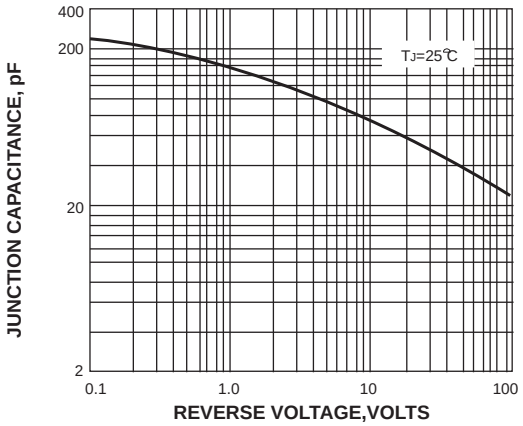
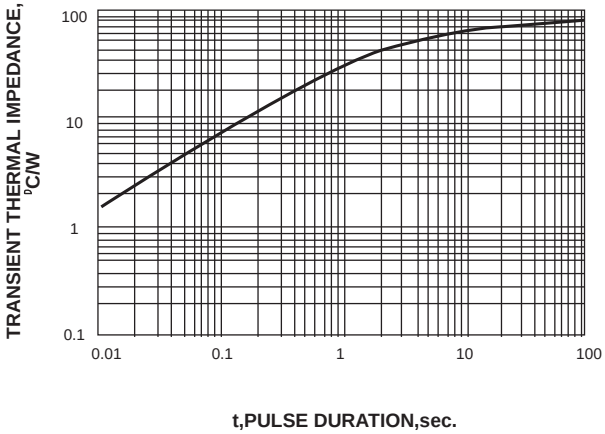


FIG. 6-TYPICAL TRANSIENT THERMAL IMPEDANCE



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